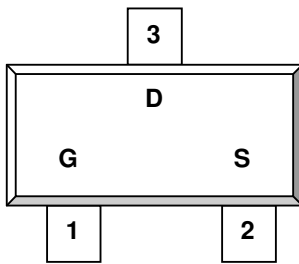


**DESCRIPTION**

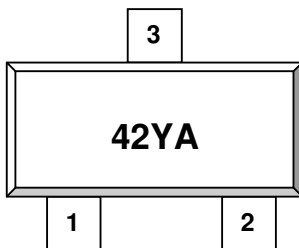
The ST2300SRG is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other batter powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

**PIN CONFIGURATION  
SOT-23**


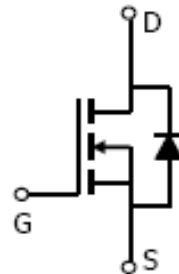
1.Gate 2.Source 3.Drain

**FEATURE**

- 20V/6.0A,  $R_{DS(ON)} = 35m\Omega$  (Typ.) @ $V_{GS} = 10V$
- 20V/5.0A,  $R_{DS(ON)} = 48m\Omega$  @ $V_{GS} = 4.5V$
- 20V/4.5A,  $R_{DS(ON)} = 90m\Omega$  @ $V_{GS} = 2.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability
- SOT-23 package design

**PART MARKING  
SOT-23**


Y: Year Code A: Process Code


**ORDERING INFORMATION**

Part Number	Package	Part Marking
ST2300SRG	SOT-23	42YA

※ Process Code : A ~ Z ; a ~ z

※ ST2300SRG ; S : SOT23 R : Tape Reel ; G : Pb – Free



**ST2300SRG**



N Channel Enhancement Mode MOSFET

6.0A

**ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted )**

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Continuous Drain Current (T <sub>J</sub> =150°C)	T <sub>A</sub> =25°C	I <sub>D</sub>	6.0	A
	T <sub>A</sub> =70°C		3.0	
Pulsed Drain Current		I <sub>DM</sub>	10	A
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	1.0	A
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	1.25	W
	T <sub>A</sub> =70°C		0.8	
Operation Junction Temperature		T <sub>J</sub>	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient		R <sub>θJA</sub>	140	°C/W



**ST2300SRG**



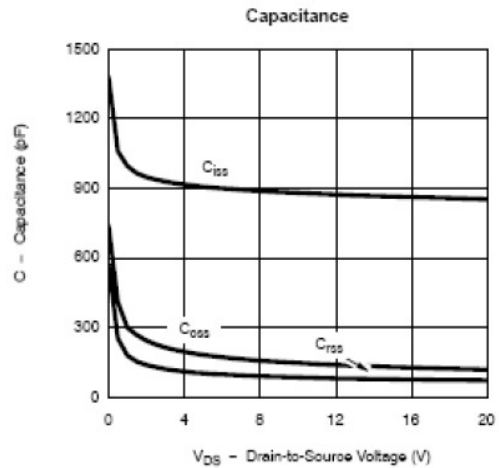
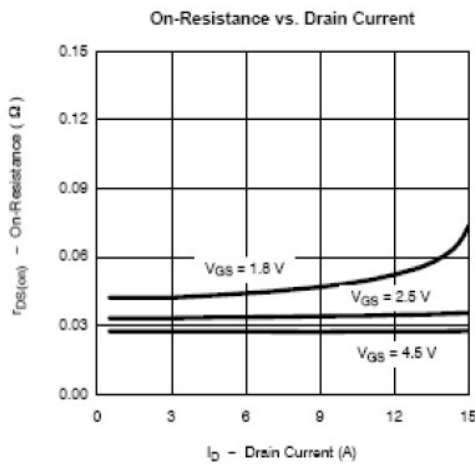
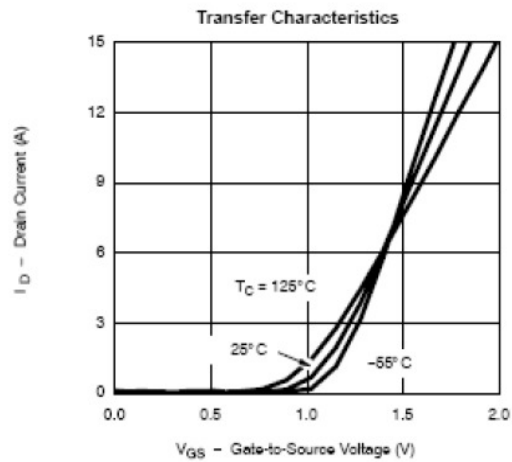
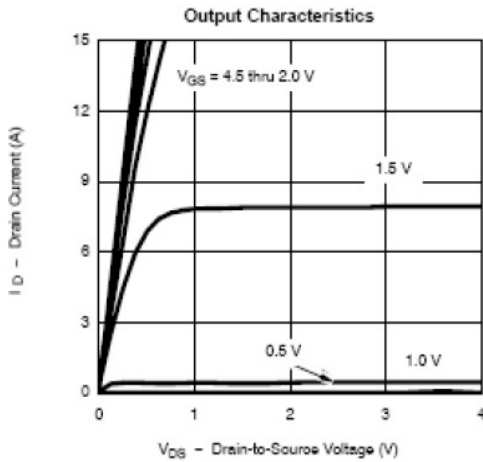
N Channel Enhancement Mode MOSFET

6.0A

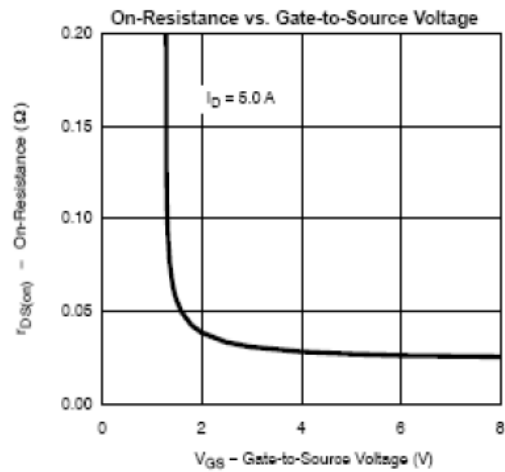
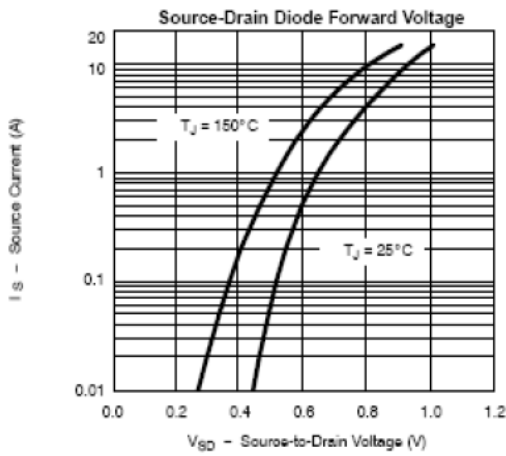
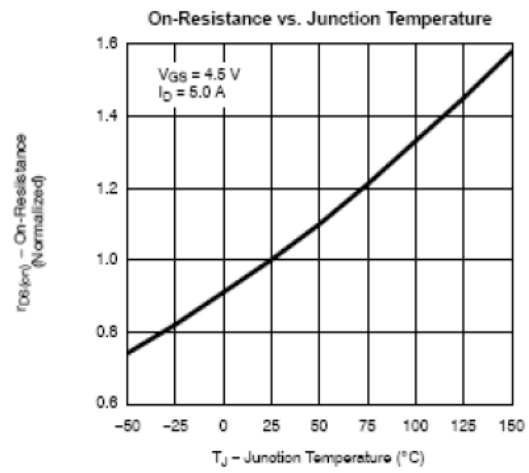
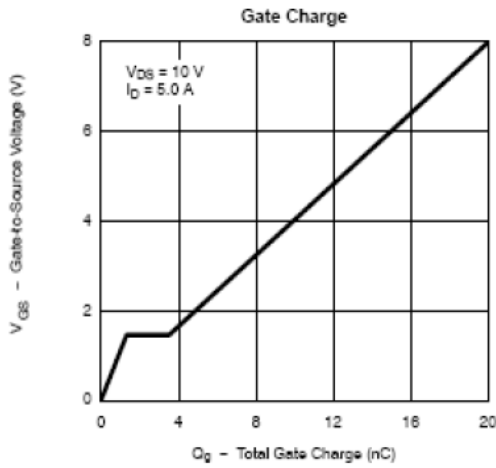
**ELECTRICAL CHARACTERISTICS** ( Ta = 25°C Unless otherwise noted )

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4		1.2	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=85^\circ C$			10	
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=6.0A$ $V_{GS}=4.5V, I_D=5.0A$ $V_{GS}=2.5V, I_D=4.5A$		0.035 0.048 0.090		$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS}=15V, I_D=5.0A$		30		S
Diode Forward Voltage	$V_{SD}$	$I_S=1.7A, V_{GS}=0V$		0.9	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=10V$ $V_{GS}=4.5V$ $I_D=5A$		10	13	nC
Gate-Source Charge	$Q_{gs}$			1.4		
Gate-Drain Charge	$Q_{gd}$			2.1		
Input Capacitance	$C_{iss}$	$V_{DS}=10V$ $V_{GS}=0V$ $F=1MHz$		600		pF
Output Capacitance	$C_{oss}$			120		
Reverse Transfer Capacitance	$C_{rss}$			100		
Turn-On Time	$t_{d(on)}$ $t_r$	$V_{DD}=10V$ $R_L=10\Omega$ $I_D=1A$ $V_{GEN}=4.5V$ $R_G=6\Omega$		15	25	nS
				40	60	
Turn-Off Time	$t_{d(off)}$ $t_f$			45	65	
				30	40	

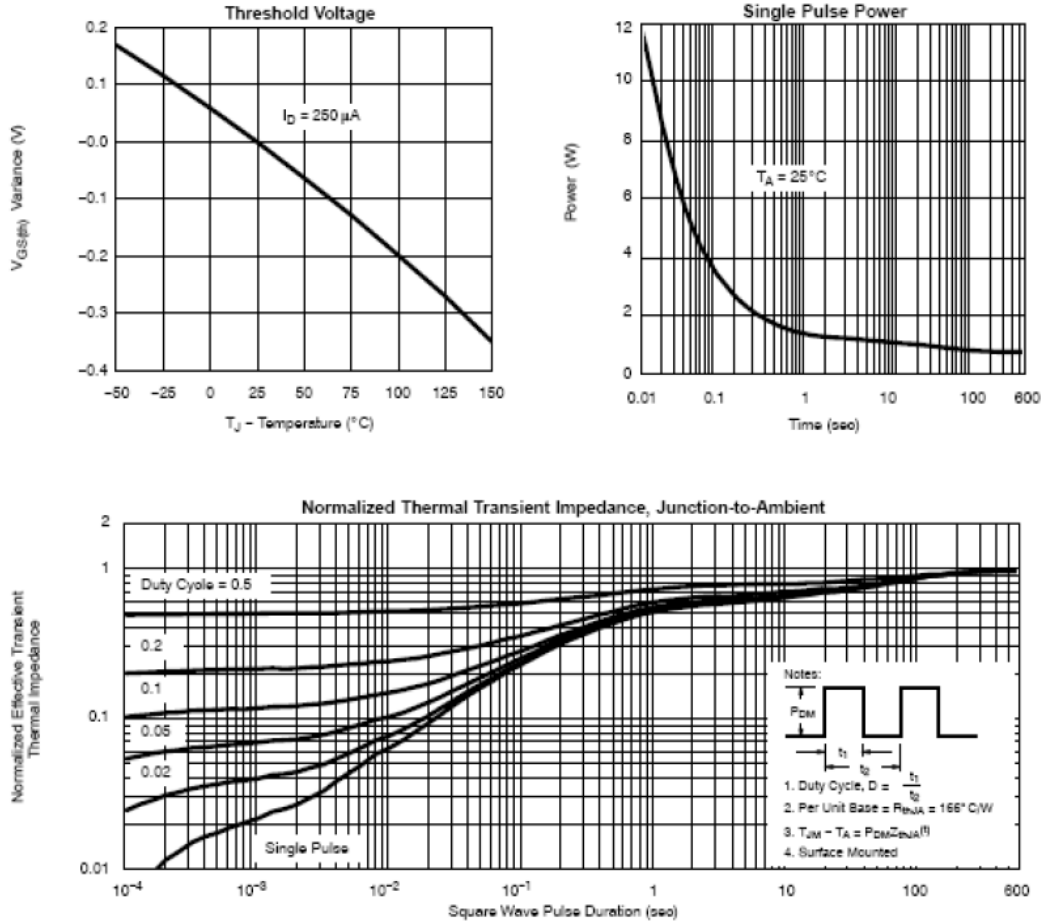
**TYPICAL CHARACTERISTICS (25°C Unless noted)**

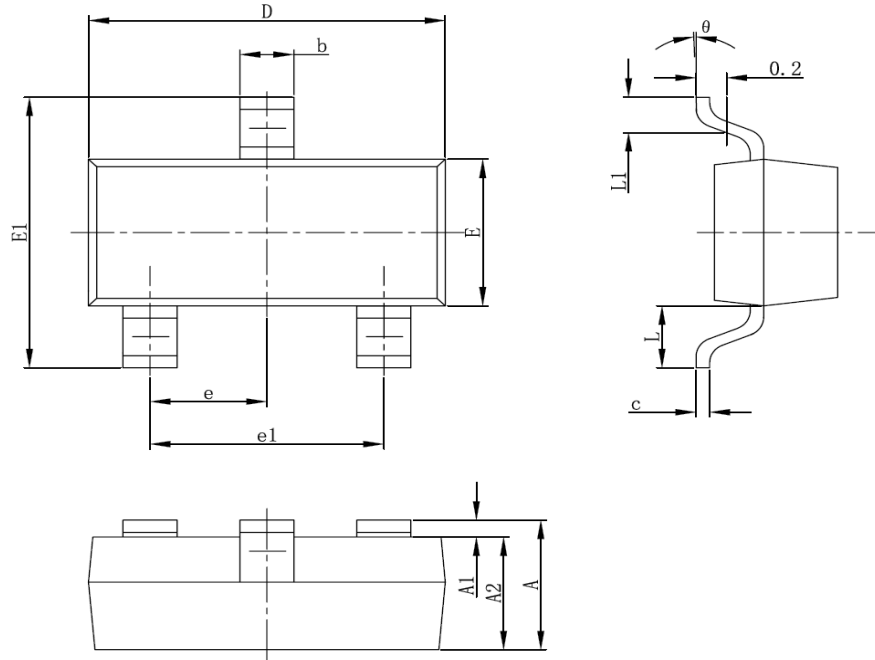


**TYPICAL CHARACTERISTICS** (25°C Unless noted)



**TYPICAL CHARACTERISTIC**



**SOT-23 PACKAGE OUTLINE**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°